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拓電半導體

自主封測 品質把控 售後保障

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BAV70-TD

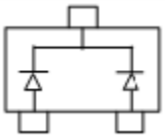
產品規格說明書

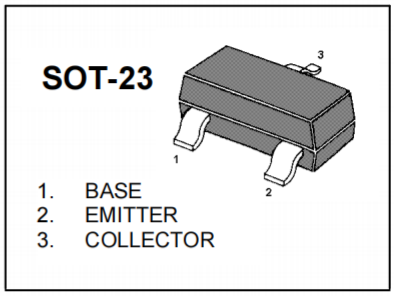
TDSEMIC

BAV70 SWITCHING DIODES

FEATURES

Fast Switching Speed
For General Purpose Switching Applications
High Conductance





MARKING: A4

Maximum Ratings @T_A=25℃

Paramet	Symbol	Lim	Unit
Reverse voltage	V_R	8	V
Forward Current	I_F	2	mA
Peak Forward Surge Current	$I_{FM(surge)}$	5	mA
Power Dissipation	P_D	2	mW
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	5	℃/W
Junction temperature	T_J	1	℃
Storage temperature range	T_{STG}	-55-150	℃

Electrical Characteristics @T_A=25℃

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Reverse Breakdown Voltage	V_R	80			V	I_R=100μA
Forward voltage	V_{F1}			0.715	V	I_F=1mA
	V_{F2}			0.855	V	I_F=10mA
	V_{F3}			1	V	I_F=50mA
	V_{F4}			1.25	V	I_F=150mA
Reverse current	I_R			2.5	μA	V_R=80V
Capacitance between terminals	C_T			1.5	pF	V_R=0, f=1MHz
Reverse recovery time	t_{rr}			6	ns	I_F = I_R = 10mA, Irr= 0.1 x I_R, R_L = 100Ω

Typical Characteristics BAV70

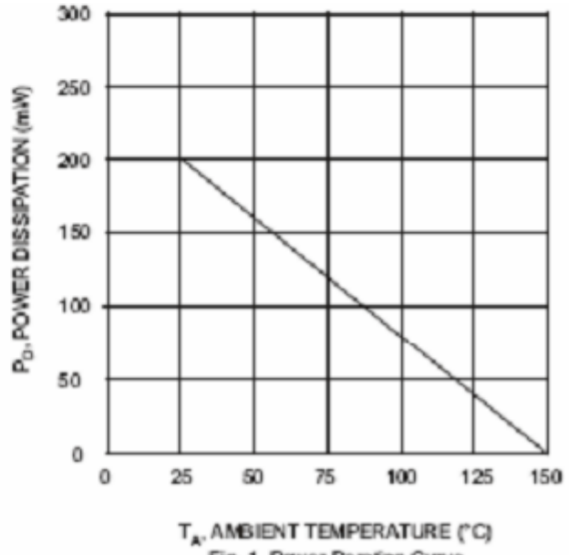


Fig. 1 Power Derating Curve

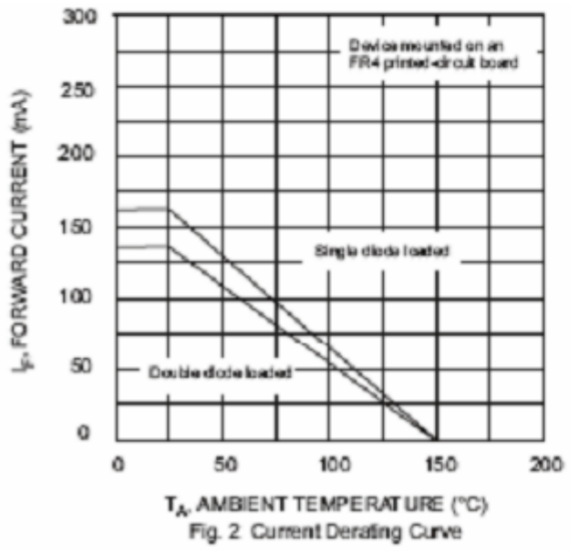


Fig. 2 Current Derating Curve

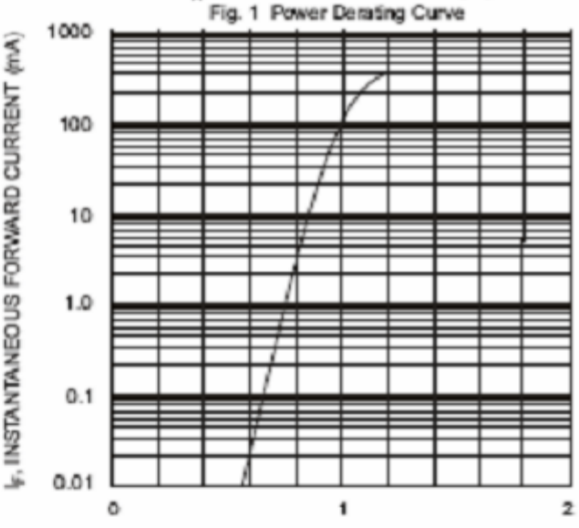


Fig. 3 Typical Forward Characteristics

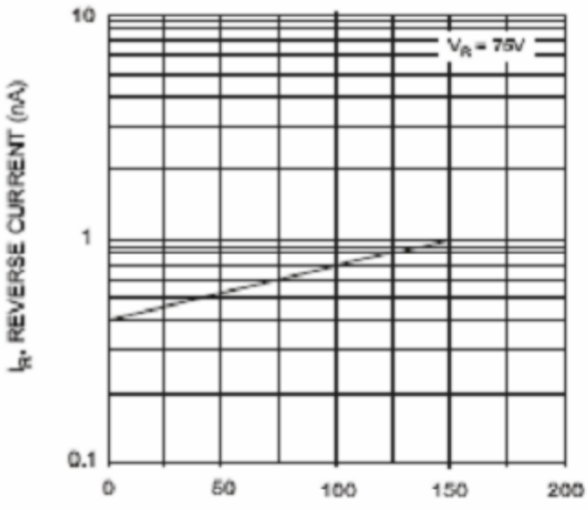
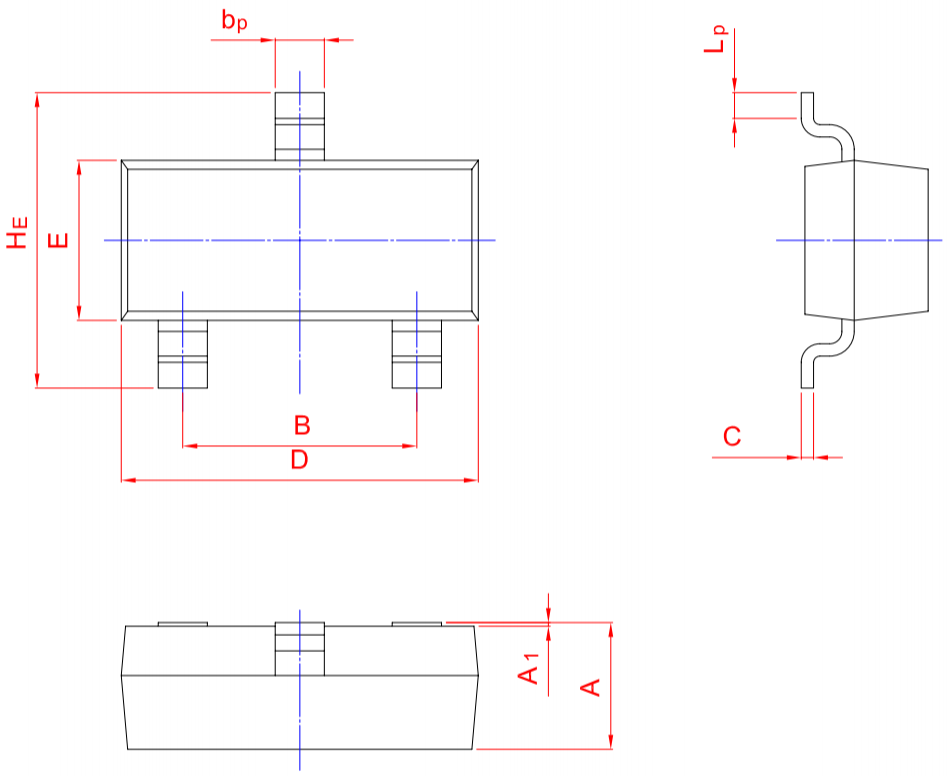


Fig. 4 Typical Reverse Characteristics

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads **SOT-23**



UNIT	A	B	bp	C	D	E	HE	A1	Lp
mm	1.40 0.95	2.04 1.78	0.50 0.35	0.19 0.08	3.10 2.70	1.65 1.20	3.00 2.20	0.100 0.013	0.50 0.20